

ABSTRACT

A method for generating an organic plug within a via is described. The via resides in an integrated circuit (IC) structure having a silicon containing dielectric material. The method for generating the organic plug includes applying an organic compound such as a bottom antireflective coating. The organic compound occupies the via. The method then proceeds to feed a nitrous oxide (N_2O) gas into a reactor and generates a plasma in the reactor. A significant portion of the organic compound is removed leaving behind an organic plug to occupy the via. The organic plug is typically generated during dual damascene processing.